

Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from, Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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Standard Rectifier Module

R	3~ Rectifier			
V_{RRM}	=	800 V		
I_{DAV}	=	35 A		
I _{FSM}	=	400 A		

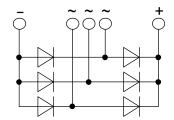
3~ Rectifier Bridge

Part number

VUO35-08NO7







Features / Advantages:

- Package with DCB ceramic
- Improved temperature and power cycling
- Planar passivated chips
- Very low forward voltage drop
- Very low leakage current

Applications:

- Diode for main rectification
- For three phase bridge configurations
 Supplies for DC power equipment
- Input rectifiers for PWM inverter
- Battery DC power supplies
- Field supply for DC motors

Package: PWS-A

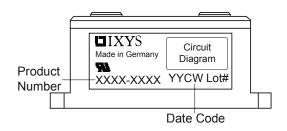
- Industry standard outline
- RoHS compliant
- Easy to mount with two screws
- Base plate: Aluminium internally DCB isolated
- Advanced power cycling



Rectifie	r				Ratings	3	
Symbol	Definition	Conditions		min.	typ.	max.	Unit
V _{RSM}	max. non-repetitive reverse bloc	king voltage	$T_{VJ} = 25^{\circ}C$			900	V
V _{RRM}	max. repetitive reverse blocking	voltage	$T_{VJ} = 25^{\circ}C$			800	V
I _R	reverse current	V _R = 800 V	$T_{VJ} = 25^{\circ}C$			40	μΑ
		$V_R = 800 V$	$T_{VJ} = 150^{\circ}C$			1.5	mΑ
V _F	forward voltage drop	I _F = 15 A	$T_{VJ} = 25^{\circ}C$			1.10	V
		$I_F = 45 A$				1.38	٧
		I _F = 15 A	T _{VJ} = 125 °C			1.01	V
		$I_F = 45 A$				1.38	V
IDAV	bridge output current	T _c = 85°C	T _{vJ} = 150°C			35	Α
		rectangular d = ⅓					
V _{F0}	threshold voltage		T _{vJ} = 150°C			0.80	V
r _F	slope resistance \(\) for power	loss calculation only				12.9	mΩ
R _{thJC}	thermal resistance junction to ca	ase				4.2	K/W
R _{thCH}	thermal resistance case to heats	sink			0.6		K/W
P _{tot}	total power dissipation		$T_{c} = 25^{\circ}C$			29	W
I _{FSM}	max. forward surge current	t = 10 ms; (50 Hz), sine	$T_{VJ} = 45^{\circ}C$			400	Α
		t = 8,3 ms; (60 Hz), sine	$V_R = 0 V$			430	Α
		t = 10 ms; (50 Hz), sine	T _{vJ} = 150°C			340	Α
		t = 8,3 ms; (60 Hz), sine	$V_R = 0 V$			365	Α
l²t	value for fusing	t = 10 ms; (50 Hz), sine	$T_{VJ} = 45^{\circ}C$			800	A²s
		t = 8,3 ms; (60 Hz), sine	$V_R = 0 V$			770	A²s
		t = 10 ms; (50 Hz), sine	T _{VJ} = 150°C			580	A²s
		t = 8,3 ms; (60 Hz), sine	$V_R = 0 V$			555	A²s
C	junction capacitance	$V_R = 400 \text{ V}; f = 1 \text{ MHz}$	$T_{VJ} = 25^{\circ}C$		10		pF



Package PWS-A					Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit	
I _{RMS}	RMS current	per terminal				100	Α	
T _{stg}	storage temperature			-40		125	°C	
T _{VJ}	virtual junction temperature			-40		150	°C	
Weight					100		g	
M _D	mounting torque			1.25		1.75	Nm	
M_{τ}	terminal torque			1.25		1.75	Nm	
d Spp/App	creepage distance on surface striking distance through air		terminal to terminal	6.5			mm	
d Spb/Apb			terminal to backside	8.5			mm	
V _{ISOL}	isolation voltage	t = 1 second	50/60 Hz, RMS; I _{ISOL} ≤ 1 mA	3000			V	
		t = 1 minute		2500			٧	

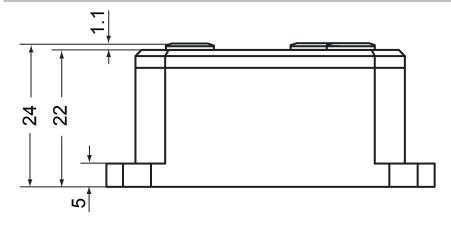


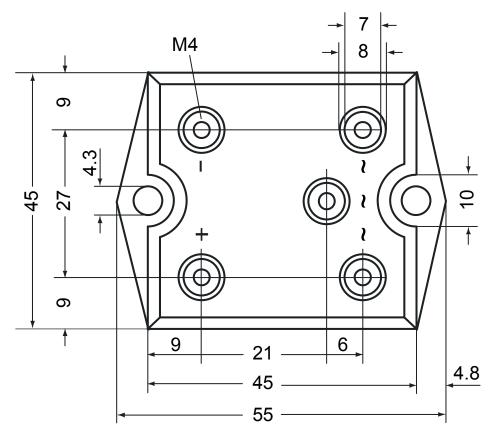
Ordering	Part Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	VUO35-08NO7	VUO35-08NO7	Box	20	502541

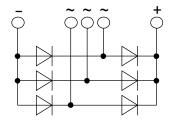
Equiva	alent Circuits for	Simulation	* on die level	T _{VJ} = 150 °C
$I \rightarrow V_0$	R_0	Rectifier		
V _{0 max}	threshold voltage	8.0		V
R_{0max}	slope resistance *	11.7		$m\Omega$



Outlines PWS-A

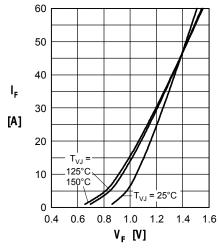


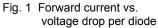






Rectifier





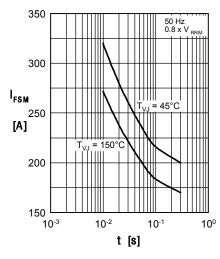


Fig. 2 Surge overload current vs. time per diode

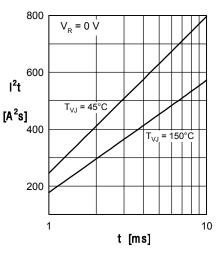


Fig. 3 I²t vs. time per diode

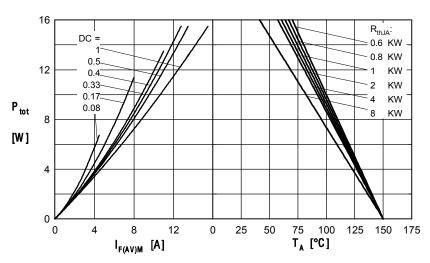


Fig. 4 Power dissipation vs. forward current and ambient temperature per diode

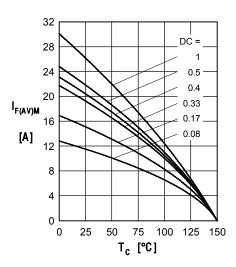


Fig. 5 Max. forward current vs. case temperature per diode

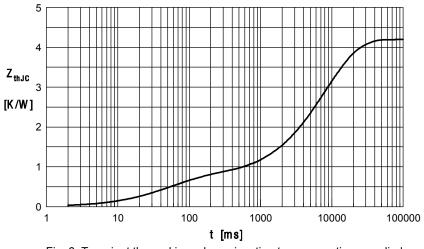


Fig. 6 Transient thermal impedance junction to case vs. time per diode $\,$

Constants for Z_{thJC} calculation:

İ	R_{th} (K/W)	t _i (s)
1	0.194	0.024
2	0.556	0.070
3	0.450	3.250
4	3.000	9.300